



K. Memory (Design & Process Technology) 분과

2019년 2월 15일(금), 09:00-10:45

Room A (아라홀, 2층)

[FA1-K] Resistive Memory I

좌장: 백승재 교수(한경대학교), 황희돈 수석(삼성전자)

<p>FA1-K-1 09:00-09:30</p>	<p>[초청] Stateful In-Memory Computing in Emerging Crossbar Memories Kyung Min Kim <i>Department of Materials Science and Engineering, KAIST</i></p>
<p>FA1-K-2 09:30-09:45</p>	<p>High Performance of 1D-1R Memristor through Localized Ti-Doped NiO Layer with InZnOx/CuOx Oxide Diode Minho Song^{1,2}, Taekwang Kim¹, David H. Seo², Sunae Seo¹, and Myoung-Jae Lee² <i>¹Department of Physics, Sejong University, ²Research Institute, DGIST</i></p>
<p>FA1-K-3 09:45-10:00</p>	<p>Design and Switching Characteristics Analysis of 3D Vertical W/SiN_x/n⁺-Si/p-Si 1D1R Unipolar RRAM Chae Soo Kim¹, Suhyun Bang¹, Tae-Hyeon Kim¹, Kyungkyu Min¹, Min-Hwi Kim¹, Dong Keun Lee¹, Yeon-Joon Choi¹, Kyungho Hong¹, Sungjun Kim², and Byung-Gook Park¹ <i>¹Department of Electrical and Computer Engineering, Seoul National University, ²School of Electronics Engineering, Chungbuk National University</i></p>
<p>FA1-K-4 10:00-10:15</p>	<p>Effect of Doping in HfO_x Based ReRAM Sung Yeon Ryu¹, Hee Ju Yun¹, Woo Young Park², Soo Gil Kim², Jaehyun Han², Se Ho Lee², and Byung Joon Choi¹ <i>¹Department of Materials Science and Engineering, Seoul National University of Science and Technology, ²SK Hynix</i></p>
<p>FA1-K-5 10:15-10:30</p>	<p>Forming-Free Gradual Resistance Switching Properties of Al₂O₃/AZO Junction with Various Al₂O₃ Thicknesses Taekwang Kim, Somyeong Shin, Hyewon Du, Minho Song, Seonyeong Kim, Hansung Kim, Dayin Kang, and Sunae Seo <i>Department of Physics, Sejong University</i></p>
<p>FA1-K-6 10:30-10:45</p>	<p>Resistive Switching Characteristics Improvement in a TiO₂-Based ReRAM Device by Nitrogen Doping Euyjin Park, Jaehyeun Park, Donggyu Jin, Kyu Hyun Han, and Hyun-Yong Yu <i>School of Electrical Engineering, Korea University</i></p>